

 <p>INFORMATION DISCLOSURE CITATION (Use several sheets if necessary) FEB 25 2004</p>		Docket Number (Optional) OKI.227	Application Number NEW
		Applicant(s) Norio HIRASHITA et al.	
		Filing Date APRIL 5, 2001	Group Art Unit TO BE REASSIGNED
		OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
EXAMINER INITIAL	TRADEMARK	<p>Deep sub-0.1 um MOSFET's with Very Thin SOL Layer for Ultra-Low Power Applicants, Information and Communication Engineers C-II Vol. J81-C-II No. 3, pp. 313-319, August 1998.</p> <p>Optimization of Series Resistance in Sub-0.2 um SOI MOSFET's, IEEE Electron Device letters, VOL. 15, No. 9, September 1994, p. 363-365.</p> <p>Optimization of series resistance in Sub-0.2 um SOI MOSFET's, 1993 IEEE, pp. IEDM93-723-726-IEDM 93.</p>	
<i>gld</i>	A		
<i>gld</i>	B		
<i>gld</i>	C		
EXAMINER <i>Julio L. Maldonado</i>		DATE CONSIDERED <i>05/07/2004</i>	
<p>*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance as not considered. Include copy of this form with next communication to applicant.</p>			

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